

150V N-Ch Power MOSFET

V_{DS}	150
$R_{\theta JC}$ TO-220F	8.8
I_D (Silicon Limited)	A

Absolute Maximum Ratings at T_j	Symbol	Conditions	Value	Unit
Continuous Drain Current (Silicon Limited)	I_D	T_C	50	A
		T_C	35	
Drain to Source Voltage	V_{DS}	-	150	
Gate to Source Voltage	V_{GS}	-	± 20	V
Pulsed Drain Current	I_{DM}	-	400	
Power Dissipation	P_D	T_{CT}	333	W
		T_{stg}	-55 to 175	

Absolute Maximum Ratings	Symbol	Max	Unit
Thermal Resistance Junction-Case			

Electrical Characteristics at T_j
Static Characteristics

X Q O H V V R W K H U Z L V H V S H F L I L H G

Parameter

min W \& max

Drain to Source Breakdown Voltage $V_{(BR)DSS}$

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)LJ 7\SLFDO 2XWSXW & KDUDFWHULVWL

Figure 2. On-Resistance vs. Gate-Source Voltage

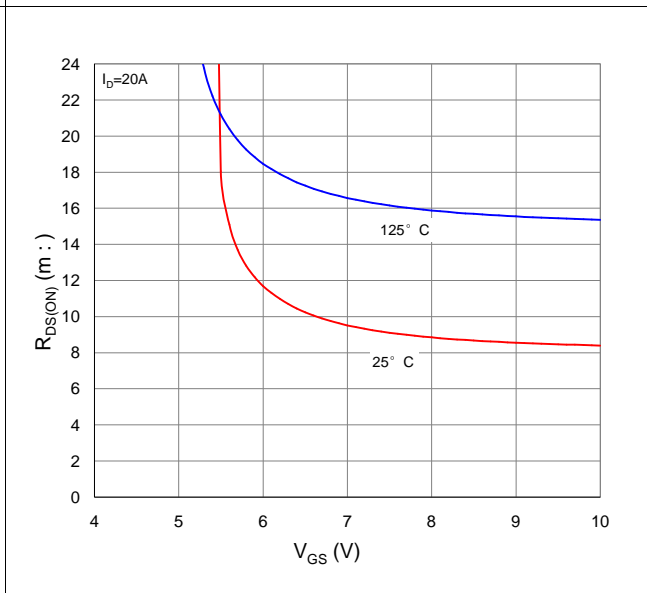
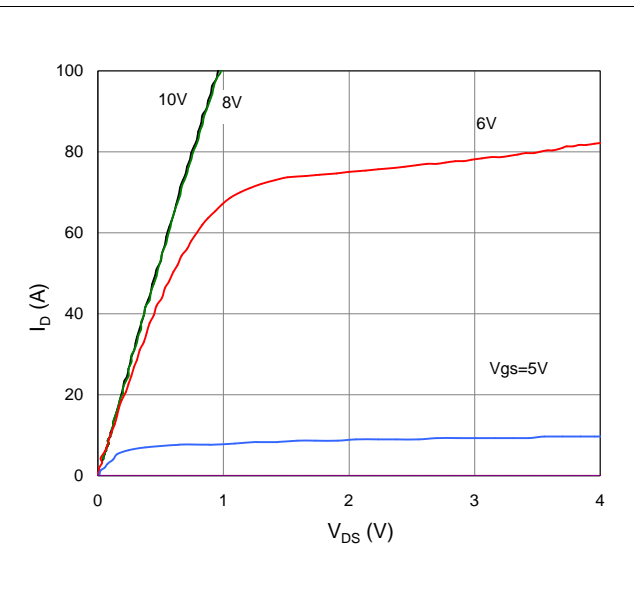
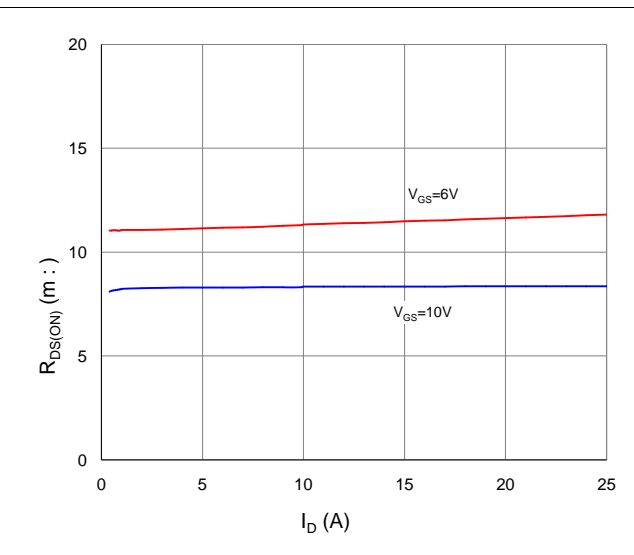
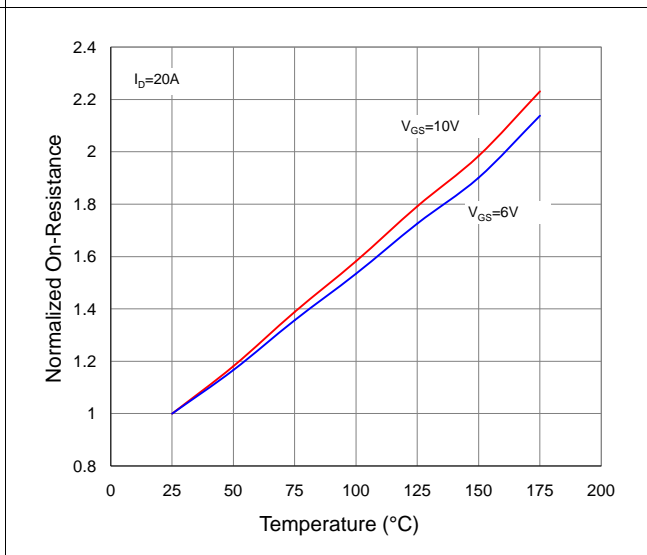


Figure 3. On-Resistance vs. Drain Current and Gate Voltage

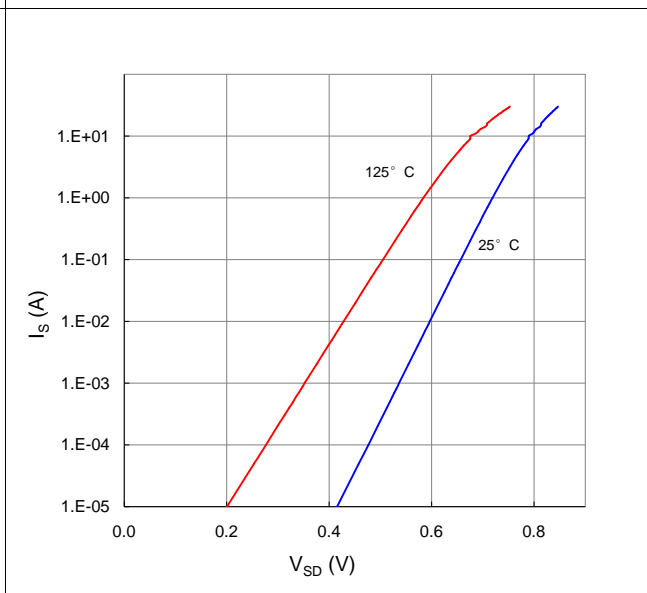
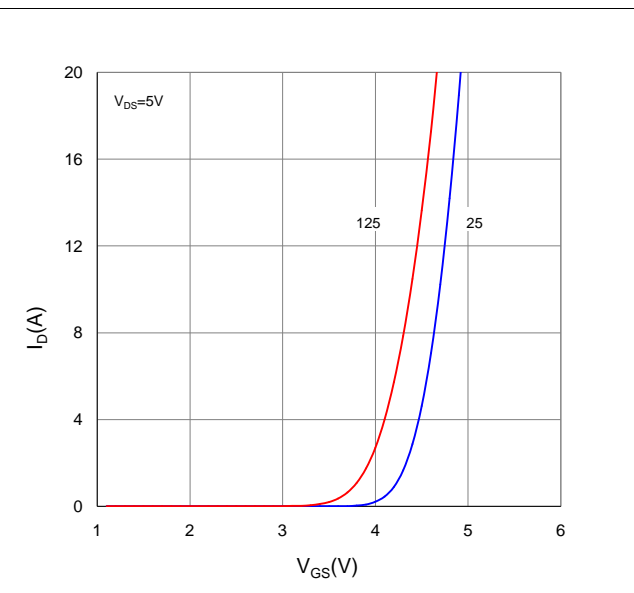


)LJXUH 1RUPDOLJHG 2Q 5HVLVWDQFH YV -XQFWLFR



)LJXUH 7\SLFDO 7UDQVIHU & KDUDFWHULVWL

)LJXUH 7\SLFDO 6RXUFH 'UDLQ 'LRGH)RUZDUG 9R





)LJXUH 7\SLFDO *DWH &KDUJH YV *DWNLW/RU6R XU7AS LFFDOWDDSDFLWDQFH YV 'UDLQ WR 6RX

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)LJXUH 0D[LPXP 6DIH 2SHUDWLQJ \$UHD)LJXUH 0D[LPXQ 'UDLQ &XUUHQW YV &DVH 7HPSH

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)LJXUH 1RUPDOLJHG 0D[LPXP 7UDQVLHQW 7KHUPDO ,PSHGDQFH -XQFWLR

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TO-220F, 3 leads

